



**MOTOROLA**  
**Semiconductors**

BOX 20912 • PHOENIX, ARIZONA 85036

**MV2201 • MV2203**  
**MV2205 • MV2209**

VVC

### AFC SILICON EPICAP\* DIODES

... designed specifically for the high volume AFC applications of FM Radio and TV, utilizing the economical PLASTIC PACKAGE.

- Very High Q with Guaranteed Minimum Values
- Guaranteed Uniformity with Minimum and Maximum Tuning Ratio Limits, Assuring Fixed Design
- Nominal Capacitance Values — 6.8 pF Thru 33 pF — Providing Complete AFC Design Flexibility

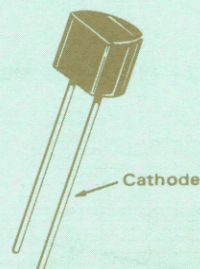
### VOLTAGE-VARIABLE CAPACITANCE DIODES

6.8–33 pF  
25 VOLTS

MAY 1969 — DS 8532

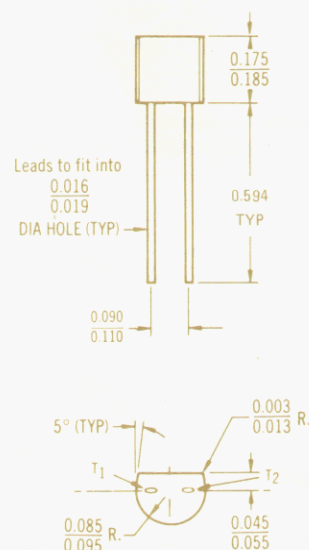
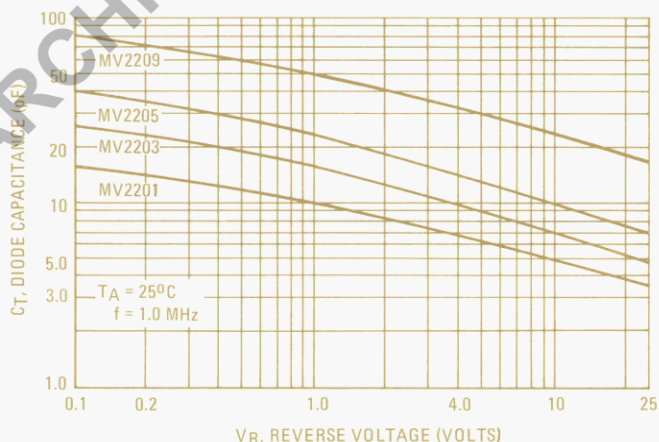
### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	25	Volts
Forward Current	$I_F$	200	mA
Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	280 2.8	mW mW/ $^\circ\text{C}$
Junction Temperature	$T_J$	+125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$



CASE 182

FIGURE 1 — DIODE CAPACITANCE versus REVERSE VOLTAGE



CASE 182

ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic—All Types	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ( $I_R = 10 \mu\text{A}$ )	$BV_R$	25		—	Vdc
Reverse Voltage Leakage Current ( $V_R = 10 \text{ Vdc}$ , $T_A = 25^\circ\text{C}$ ) ( $V_R = 10 \text{ Vdc}$ , $T_A = 85^\circ\text{C}$ )	$I_R$	— —	— —	0.5 5.0	$\mu\text{A}$
Forward Voltage Drop ( $I_F = 250 \mu\text{A}$ )	$V_F$	—	0.65	—	Vdc
Series Inductance ( $f = 250 \text{ MHz}$ , lead length $\approx 1/16''$ )	$L_S$	—	6.0	—	nH
Case Capacitance ( $f = 1.0 \text{ MHz}$ , lead length $\approx 1/16''$ )	$C_C$	—	0.18	—	pF

	$C_T$ , Diode Capacitance $V_R = 4.0 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ pF		$Q$ , Figure of Merit $V_R = 4.0 \text{ Vdc}$ , $f = 50 \text{ MHz}$	$TR$ , Tuning Ratio $C_1/C_{10}$ $f = 1.0 \text{ MHz}$	
Device	Min	Max	Min	Min	Max
MV2201	5.5	8.0	300	1.9	2.3
MV2203	8.5	11.5	200	2.0	2.4
MV2205	13	17	200	2.1	2.5
MV2209	29	37	150	2.1	2.5

FIGURE 2 — FIGURE OF MERIT versus REVERSE VOLTAGE

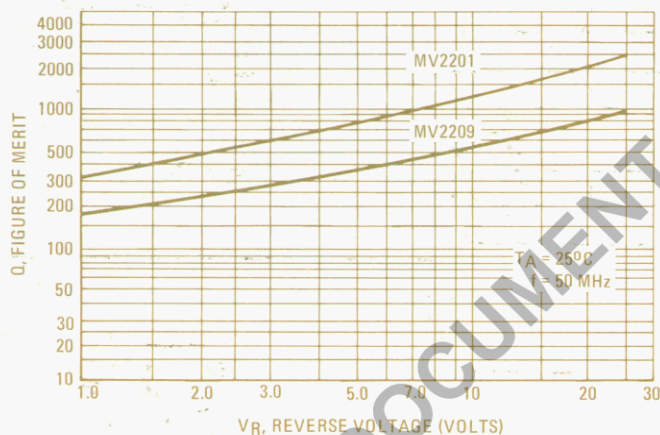


FIGURE 3 — FIGURE OF MERIT versus FREQUENCY

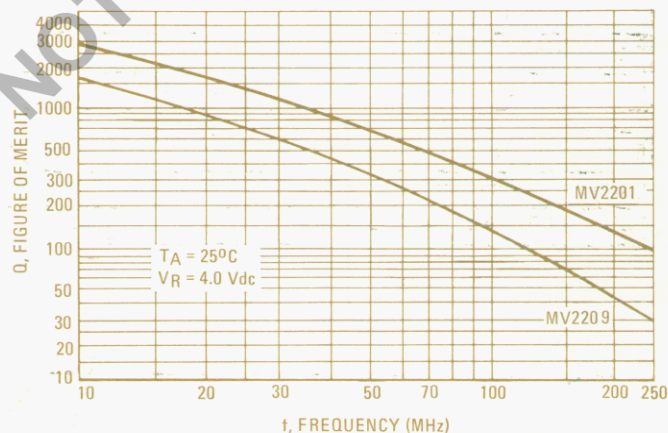
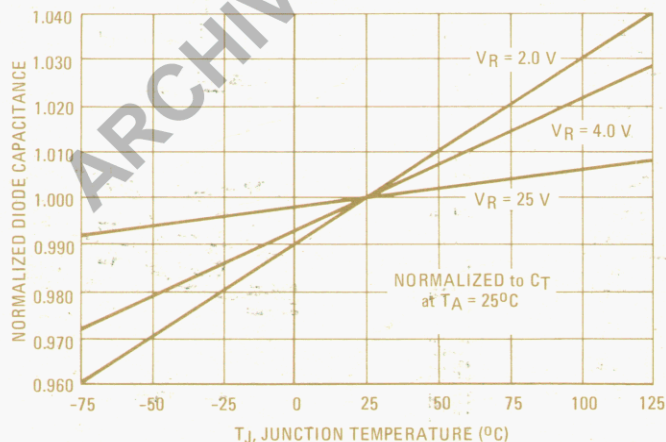


FIGURE 4 — NORMALIZED DIODE CAPACITANCE versus JUNCTION TEMPERATURE



## NOTES ON TESTING AND SPECIFICATIONS

$L_S$  is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

$C_C$  is measured on a package without a die, using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

$Q$  is calculated by taking the  $G$  and  $C$  readings of an admittance bridge, such as Boonton Electronics Model 33AS8, at the specified frequency and substituting in the following equation:

$$Q = \frac{2\pi f C}{G}$$



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